

Plymouth, Minnesota USA

# High Temperature Analog to Digital Converter Reliability Testing



#### HTADC12 - High Temp 12-Bit ADC Reliability Study

- It is common practice to characterize and compensate initial measurement errors in down-hole tools
- Component drift over time and temperature cycling are therefore just as important to know/predict as time-zero accuracy
- Parametric shifts affecting post-compensation accuracy are presented for a 12-bit ADC from samples stressed by 250°C bias plus temperature cycling from -65°C to 200°C
- Mechanical / Assembly data is also presented

# HTADC12 Block Diagram



- 12 Bit Successive Approximation ADC
- Temperature range: -55°C to 225°C
- 5V supply: 0V to VREF full-scale input range
- On-chip 2.5V Reference
- On-chip buffer op amp
- 4MHz internal clock for conversion
- 10µs conversion time
- Parallel or Serial data outputs
- 28 or 14 pin DIP package configurations

# Life-test/Temp-Cycle/Test Flowchart

#### 1500 Hours at 250C + 1000 Temp-cycles (-65°C to 200°C)



# **Assembly Details**

#### Ceramic 28-lead DIP package

- Multi-layer alumina ceramic
- Kovar lid / Furnace seal
- Alloy 42 side-brazed leads
- Gold over nickel surface metalization
- Gold-backed SOI die
  - Die-size = 2.8mm x 2.9mm
  - Aluminum wirebond pads
- Gold-eutectic die bond
  - Gold (1% Si) die attach preform
- Aluminum ultra-sonic wedge bond
  - 1.25 mil aluminum (1.5% Si) wire

#### 14-lead package uses similar materials/flow Current production uses high-temp. adhesive die-attach



# **Life-test Fixture**

- High-temp. sockets mounted on aluminum rails.
- Wire-wound resistors
- Nickel wire/Fiberglass sheath
- Welded + Soldered connections (95/5 Pb/Sn solder)



# **Burn-in / Life-test Configuration**

- Configured for continuous conversion at Vin=half-scale
- Buffer Amp configured as voltage-follower with Vin=2.5V
- VDD = 6V (operating = 5V)
- Oven at 250°C



### **Electrical Test Parameters**

- At each electrical test point collected data using automated tester
- On-chip temperature monitored by forward drop of ESD diodes
- Test program collects DC data:
  - Buffer Amplifier offset voltage at 2.5V VIN
  - ADC offset, full-scale, and linearity errors
  - Conversion Time: Controlled by on-chip R-C oscillator
  - No-load output of the 2.5V reference

w Conversion time and VREF tempco/scale-factor are trimmed at wafer test

#### Note:

- The ADC has superior INL/DNL performance at high temp relative to room temperature
- Cross-over from 1.1 to 2.0 LSB INL to 0.5 LSB INL is observed at »160°C
- This is attributed to design attributes rather than process/device stability

225°C results provide best insight into performance and stability of the technology

# Life-test results (225°C data)



- These results are obtained with an external reference applied (i.e., independent of any VREF drift)
- General trend:
  - Full-scale/Offset errors show an initial shift (within 168 hrs) in opposite directions
  - Indicative of an "end-point shift" in the transfer function

# Life-test Results (225°C data)



- Buffered 2.5V reference is generally applied as the ADC Reference Input and defines the full-scale input range
- Buffer amplifier may be used to drive the ADC input
  - In that case shift in buffer amplifier offset adds to ADC offset

# Temp. Cycling Results (25°C Data)



- Above charts compare data prior to T-cycling (blue) to data obtained after T-cycling (Red)
- Full-scale/Offset shifts in opposite directions are observed
  - Indicative of an "end-point shift" in the transfer function

# Integral Non-Linearity (INL) Results

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#### • 1500 hours at 250°C + 1000 T-cycles does not significantly change linearity

# **Electrical Parameter Summary**

Predicted Accuracy Degradation from Results			
	Typical	Worst-case	Units
Drift after 1500 hrs @ 250C			
ADC Offset and Full-scale	0.81	1.74	LSB's
Buffer Amplifier	0.36	0.74	LSB's
VREF	3.1	4.6	LSB's
Additional Drift from 1000 T-Cycles			
ADC Offset and Full-scale	1.26	1.46	LSB's
Total from above sources	5.53	8.54	LSB's
	0.14	0.21	% of FS

- Reference drift is dominant error source
- Followed by ADC Offset/Full-scale drift with temperature cycling
- Resolution/Linearity is not significantly impacted

### **Mechanical / Assembly Test Results**

- All parts passed hermeticity tests
  - Mil-Std 883, TM1014, conditions A1, C1
  - 1500 Hours at 250C, 100 Temperature Cycles (-65°C, 200°C)
- Wire-bond pull tests passed
  - Mil-Std 883, TM1011, condition D
  - 1500 hrs @ 250C, 1000 T-cycles
  - 2 packages, 70 wires pulled
  - Ave. pull-strength = 5.7 grams, Minimum = 4.9 grams
  - Pass criteria is 2.0 grams
- Die-shear tests passed
  - Mil-Std 883, TM1019
  - 2-die tested : 23.3 kgf / 30.2 kgf shear strength
  - Pass criteria is 1.0 kgf

- Testing has been completed to provide benchmark data/results for predicting ADC performance over time at high temp. with temperature cycling
- Mechanical integrity, functionality, and linearity are stable over the test conditions
  - -1500 Hours at 250C, 1000 Temperature Cycles (-65°C, 200°C)
- Total compensated accuracy degradation is 5.5 LSB's typical (3.3mV for a 2.5V full-scale range)
  - -Dominated by reference voltage drift
- Potential for marginal improvement from extended burn-in/preconditioning

#### Honeywell High Temperature Website

#### www.hightempsolutions.com

Bruce Ohme bruce.ohme@honeywell.com Plymouth, Minnesota USA